ON Semiconductor

Is Now

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and onsemi and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

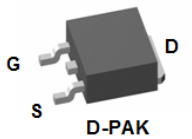
Downloaded from Arrow.com.

ON Semiconductor®

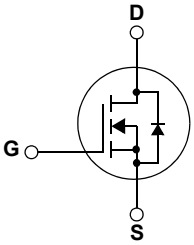
FDD120AN15A0-F085

N-Channel Power Trench® MOSFET

150V, 14A, 120mΩ



D-PAK
(TO-252)



Features

- Typ $r_{DS(on)}$ = 90.5mΩ at V_{GS} = 10V, I_D = 4A
- Typ $Q_{g(tot)}$ = 11.3nC at V_{GS} = 10V, I_D = 4A
- UIS Capability
- RoHS Compliant
- Qualified to AEC Q101

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Integrated Starter/alternator
- Primary Switch for 12V Systems

MOSFET Maximum Ratings T_J = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage		150	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current - Continuous (V_{GS}=10) (Note 1)	T_C = 25°C	14	A
	Pulsed Drain Current	T_C = 25°C	See Figure4	
E_{AS}	Single Pulse Avalanche Energy	(Note 2)	122	mJ
P_D	Power Dissipation		65	W
	Derate above 25°C		0.43	W/°C
T_J, T_{STG}	Operating and Storage Temperature		-55 to + 175	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case		2.3	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance Junction to Ambient	(Note 3)	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD120AN15A0	FDD120AN15A0-F085	D-PAK(TO-252)	330mm	12mm	2500 units

Notes:
1: Current is limited by bondwire configuration.
2: Starting T_J = 25°C, L = 27mH, I_{AS} = 3A, V_{DD} = 100V during inductor charging and V_{DD} = 0V during time in avalanche
3: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in^2 pad of 2oz copper.

©2013 Semiconductor Components Industries, LLC.

Downloaded from Arrow.com.

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
Off Characteristics							
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V		150	-	-	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=150V, V_{GS} = 0V	T_J = 25°C	-	-	1	μA
			T_J = 175°C(Note 4)	-	-	1	mA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V		-	-	±100	nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA		2.0	3.0	4.0	V
$r_{DS(on)}$	Drain to Source On Resistance	I_D = 4A, V_{GS}= 10V	T_J = 25°C	-	90.5	120	mΩ
			T_J = 175°C(Note 4)	-	227	302	mΩ
Dynamic Characteristics							
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz		-	743	-	pF
C_{oss}	Output Capacitance			-	85	-	pF
C_{rss}	Reverse Transfer Capacitance			-	20	-	pF
R_g	Gate Resistance	f = 1MHz		-	3.4	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	V_{GS} = 0 to 10V	V_{DD} = 75V I_D = 4A	-	11.3	14	nC
$Q_{g(th)}$	Threshold Gate Charge	V_{GS} = 0 to 2V		-	1.4	1.6	nC
Q_{gs}	Gate to Source Gate Charge			-	3.1	-	nC
Q_{gd}	Gate to Drain “Miller“ Charge			-	2.6	-	nC

Switching Characteristics

t_{on}	Turn-On Time	V_{DD} = 75V, I_D = 4A, V_{GS} = 10V, R_{GEN} = 24Ω	-	-	31	ns
$t_{d(on)}$	Turn-On Delay Time		-	14	-	ns
t_r	Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	34	-	ns
t_f	Fall Time		-	15	-	ns
t_{off}	Turn-Off Time		-	-	59	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	I_{SD} = 4A, V_{GS} = 0V	-	-	1.25	V
		I_{SD} = 2A, V_{GS} = 0V	-	-	1.2	V
T_{rr}	Reverse Recovery Time	I_F = 4A, dI_{SD}/dt = 100A/μs, V_{DD}=120V	-	46	60	ns
Q_{rr}	Reverse Recovery Charge		-	94	108	nC

Notes:

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

Downloaded from Arrow.com.

Typical Characteristics

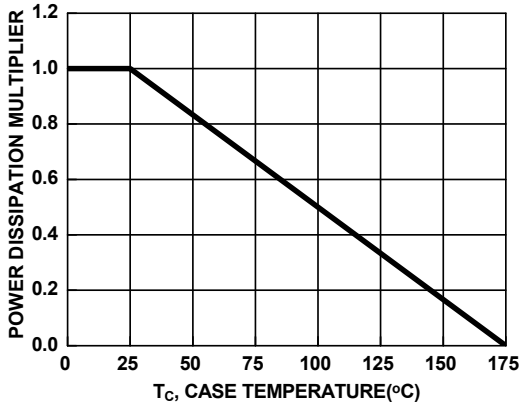


Figure 1. Normalized Power Dissipation vs Case Temperature

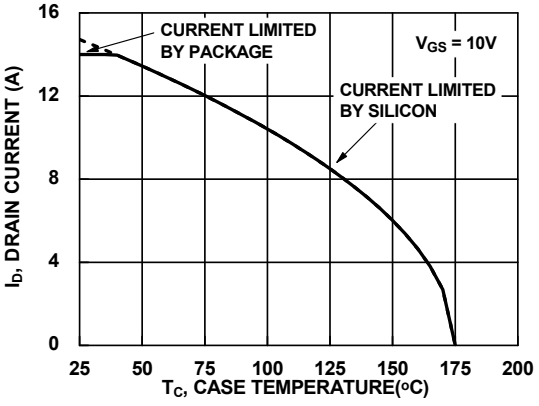


Figure 2. Maximum Continuous Drain Current vs Case Temperature

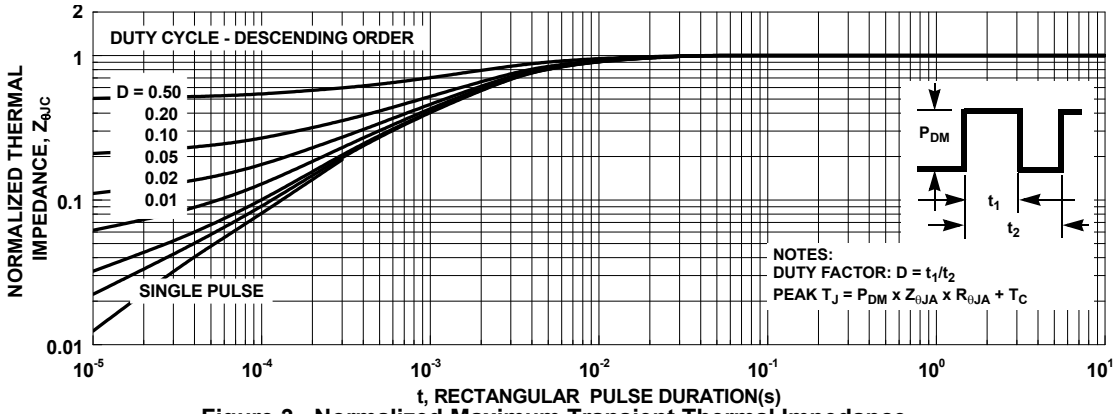


Figure 3. Normalized Maximum Transient Thermal Impedance

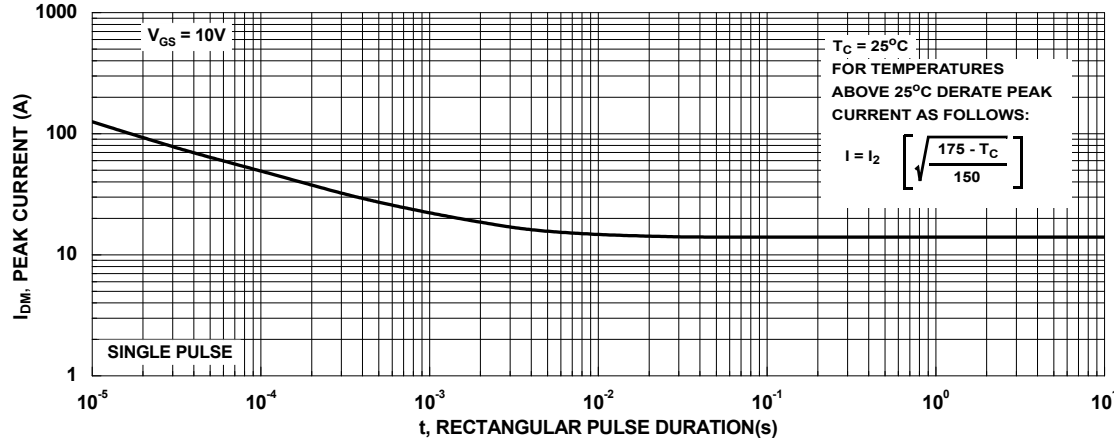


Figure 4. Peak Current Capability

Downloaded from Arrow.com.

Typical Characteristics

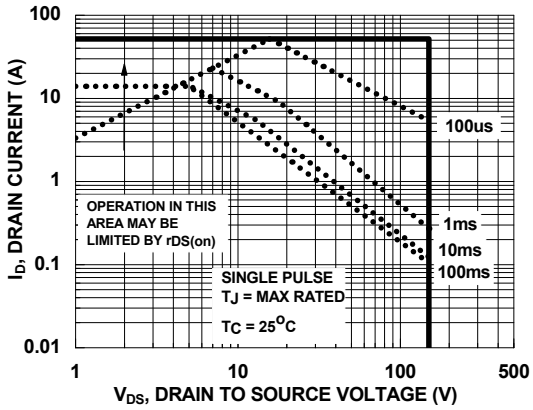
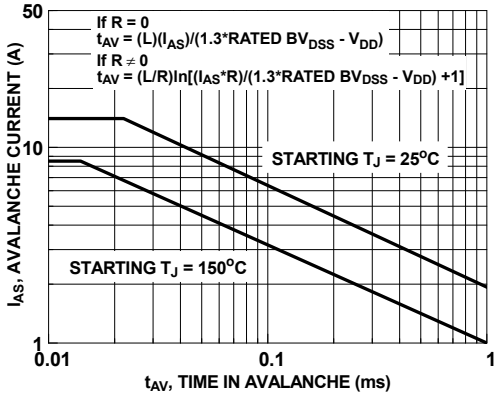


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

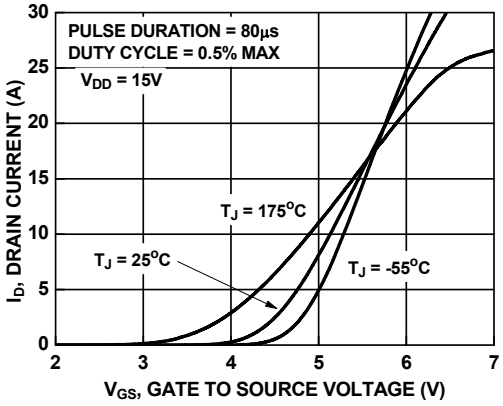


Figure 7. Transfer Characteristics

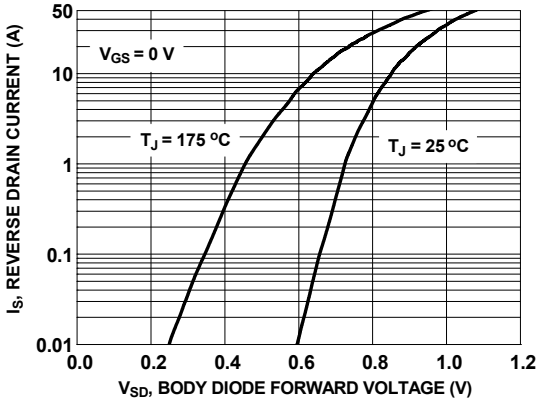


Figure 8. Forward Diode Characteristics

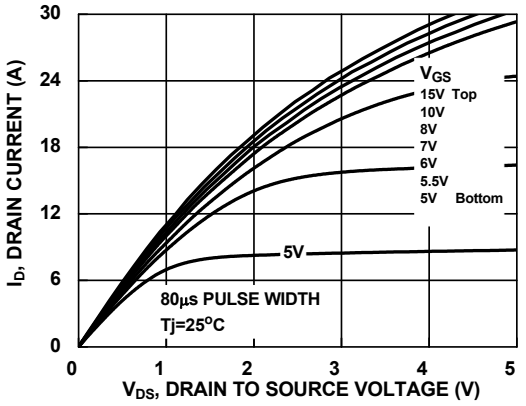


Figure 9. Saturation Characteristics

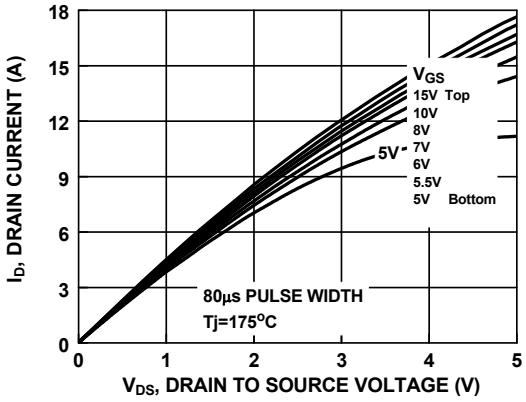


Figure 10. Saturation Characteristics

Downloaded from Arrow.com.

Typical Characteristics

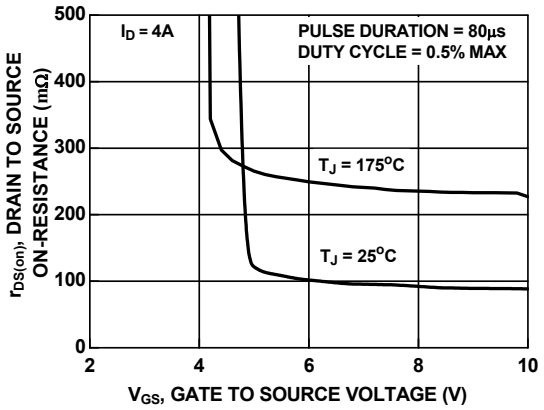


Figure 11. Rdson vs Gate Voltage

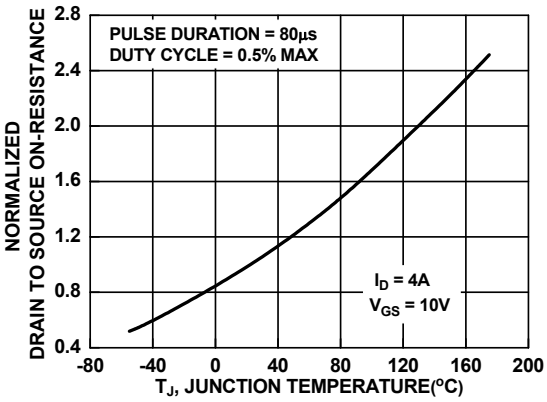


Figure 12. Normalized Rdson vs Junction Temperature

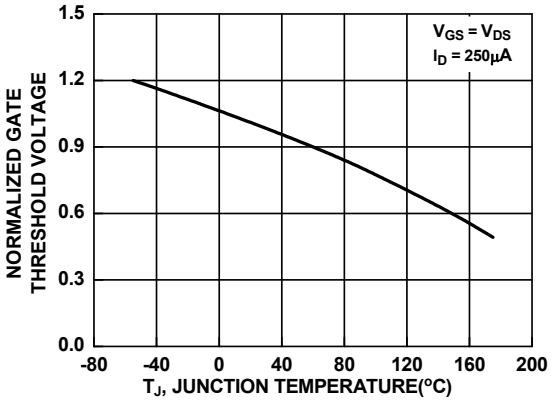


Figure 13. Normalized Gate Threshold Voltage vs Temperature

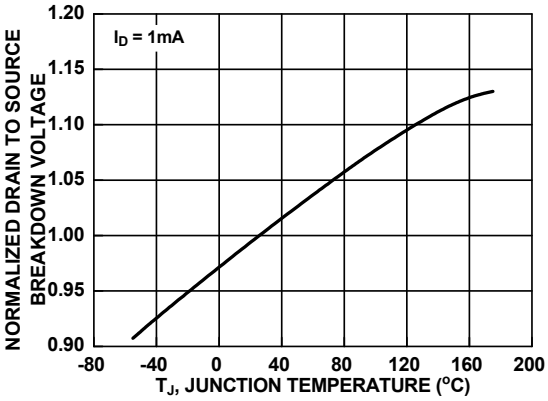


Figure 14. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

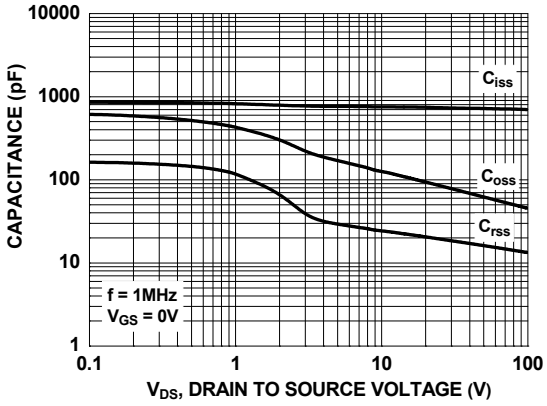


Figure 15. Capacitance vs Drain to Source Voltage

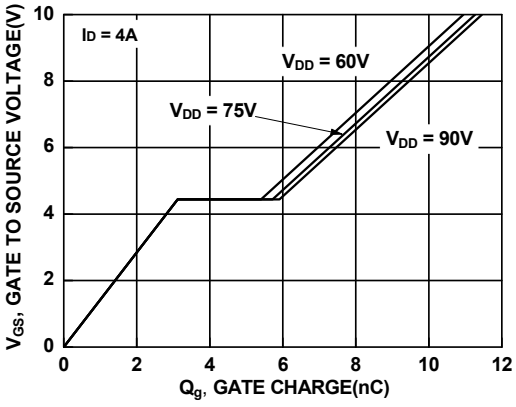


Figure 16. Gate Charge vs Gate to Source Voltage

Downloaded from Arrow.com.

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Downloaded from Arrow.com.